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Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	10/
				Filing Date	02/22/2002
				First Named Inventor	Dr. Dietmar KRUEGER
				Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	7040-53

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code 2 (if known)			
/	AA	US-4563807	01/14/1986	Sakai	
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. 1	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code 3	-Number 4	-Kind Code 5 (if known)				
/	BA	WO	98/26457	A1	06/18/1998	Lippert		

Examiner Signature		Date Considered	12/03
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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PTO/SB/08B (10-01)

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		Filing Date	02/22/2002
		First Named Inventor	Dr. Dietmar KRUEGER
		Group Art Unit	
		Examiner Name	
Sheet 1 of 1	Attorney Docket Number	7040-53	

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
CA		WEIR, ET AL, "Low temperature homoepitaxy on Si (111)," Appl.Phys.Lett., American Institute of Physics (USA), Vol. 59 ( No. 2), p. 204-206, ( July 8, 1991).	
CB		LIPPERT, ET AL., "Optimized Processing for Differentially MBE-Grown SiGe(C) Devices," Preparation and Characterization, Elsevier Sequoia (Netherlands), Vol. 321 ( No. 1), ( May 26, 1998).	
CC		ABDUL-RAHIM, A. I., ET AL, "Improved Control of polysilicon emitter interfacial oxide using a UHV-compatible LPCVD cluster tool," IEEE (USA), p. 232-236, ( February 21, 1997).	
CD		AGNELLO, ET AL., "Conditions for an Oxide-Free Si Surface for Low Temperature Processing: Steady State Boundary," J.Electrochem.Soc., The Electrochemical Society, inc. (USA), Vol. 139 ( No. 10), p. 2929-2934, ( October 21, 1992).	

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	12/03

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
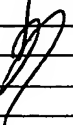
<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

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			Filing Date	02/22/2002	
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			Art Unit		
			Examiner Name		
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		Number - Kind Code <sup>2</sup> (if known)			
[Signature]	DA	US-4377421	03/22/1983	Wada	
	DB	US-5144398	09/01/1992	Morishita	
	DC	US-5285083	02/08/1994	Pulfrey	
	DD	US-5321301	06/14/1994	Sato	
	DE	US-5374481	12/20/1994	Jeng	
	DF	US-5424227	06/13/1995	Dietrich	
	DG	US-5500554	03/19/1996	Sato	
	DH	US-5659197	08/19/1997	Wei	
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		Country Code <sup>3</sup>	-Number <sup>4</sup>	-Kind Code <sup>5</sup> (if known)				
	EA	WO	88/08206	A1	10/20/1988	Smith		
	EB	EP	0 374 544	A1	06/27/1990	Fujioka		
	EC	EP	0 607 836	A2	07/27/1994	Dietrich		
	ED	EP	0 769 810	A2	04/23/1997	Kohno		
	EE	DE	30 34 078	A1	04/09/1981	Wada		
	EF	DE	197 09 181	A1	09/18/1997	Fuchs		
								

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FA		CRESSLER, ET AL, "Low frequency noise characteristics of UHV/CVD epitaxial Si- and SiGe-base bipolar transistors," IEE Electron Device Letters, IEEE (USA), Vol. 17 ( No. 1), p. 13-15, ( January 25, 1996).	
FB		NIEL, ET AL, "A 54GHz fmax implanted base 0.35 micron single poly-silicon bipolar technology," IEDM, IEEE (US), p. 807-810, ( July 25, 1997).	
FC		KNOLL, ET AL, "Si/SiGe:C heterojunction bipolar transistors in an epi-free well, single polysilicon technology," IEDM, IEEE (USA), p. 703-706, ( September 25, 1998).	
FD		HAMEL, ET AL, "Trade-off between emitter resistance and current gain in polysilicon emitter bipolar transistors with intentionally grown interfacial oxide layers," IEEE Electron Device Letters, IEEE (USA), Vol. 13 ( No. 6), p. 332-334, ( June 25, 1992).	
FE		LIPPERT, ET AL, "Optimized processing for differentially molecular beam epitaxy-grown SiGe(C) devices," Thin Solid Films, Elsevier, p. 21-25, ( March 25, 1998).	
FF		JIANG, ET AL, "77K Operation of amorphous Si/Si heterojunction bipolar transistors," Jpn J. Appl. Phys., p. 2632-2633, ( March 25, 1993).	
FG		SASAKI, ET AL, "Genuine wide-bandgap microcrystalline emitter Si-HBT with enhanced circuit gain by suppressing homocrystallization," Transactions on Electron Devices, IEEE (USA), Vol. 39 ( No. 9), p. 2132-2138, ( September 25, 1992).	
FH		KONDO, ET AL, "Analysis of emitter efficiency enhancement induced by residual stress for in situ phosphorus-doped polysilicon emitter transistors," Transactions on Electron Devices, IEEE (USA), Vol. 44 ( No. 6), p. 978-985, ( June 25, 1997).	
FI		JOUAN, ET AL, "A high-speed low 1/f noise SiGe HBT technology using epitaxially-aligned polysilicon elements," Transactions on Electron Devices, IEEE (USA), Vol. 46 ( No. 7), p. 1525-1531, ( July 25, 1999).	

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